

Features

- DDR3 functionality and operations supported as defined in the component data sheet
- 204pin, small-outline dual in-line memory module (SODIMM)
- Fast data transfer rates: PC3-8500, PC3-10600
- 1GB(128 Meg x 8), 2GB (256 Meg x 64), 4GB (512Meg x 64)
- $V_{DD} = V_{DDQ} = 1.5V \pm 0.075V$
- $V_{DDSPD} = 3.0V$ to 3.6V
- Reset pin for improved system stability
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Single or Dual rank
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Adjustable data-output drive strength
- Serial presence-detect (SPD) EEPROM
- Gold edge contacts
- Pb-free
- Fly-by topology
- Terminated control, command, and address bus

Module Specification

Part Number	Module Density & Configuration	Bandwidth	Data Rate	Timing (tCL-tRCD-tRP)
SP001GBSTU106S01(2)	1GB (128Mx64) 1Rank	PC3-8500	DDR3-1066	7-7-7
SP001GBSTU133S01(2)		PC3-10600	DDR3-1333	9-9-9
SP001GBSTU106T01(2)	1GB (128Mx64) 1Rank	PC3-8500	DDR3-1066	7-7-7
SP001GBSTU133T01(2)		PC3-10600	DDR3-1333	9-9-9
SP001GBSTU106Q01(2)	1GB (128Mx64) 2Ranks	PC3-8500	DDR3-1066	7-7-7
SP001GBSTU133Q01(2)		PC3-10600	DDR3-1333	9-9-9
SP002GBSTU106V01(2)	2GB (256Mx64) 1Rank	PC3-8500	DDR3-1066	7-7-7
SP002GBSTU133V01(2)		PC3-10600	DDR3-1333	9-9-9
SP002GBSTU106S01(2)	2GB (256Mx64) 2Ranks	PC3-8500	DDR3-1066	7-7-7
SP002GBSTU133S01(2)		PC3-10600	DDR3-1333	9-9-9
SP002GBSTU106T01(2)	2GB (256Mx64) 2Ranks	PC3-8500	DDR3-1066	7-7-7
SP002GBSTU133T01(2)		PC3-10600	DDR3-1333	9-9-9
SP004GBSTU133V01(2)	4GB (512Mx64) 2Ranks	PC3-8500	DDR3-1066	7-7-7
SP004GBSTU133V01(2)		PC3-10600	DDR3-1333	9-9-9
SP008GBSTU106V21(2)	4GB x 2 Kit Package	PC3-8500	DDR3-1066	7-7-7
SP008GBSTU133V21(2)	4GB x 2 Kit Package	PC3-10600	DDR3-1333	9-9-9

Note:

This document supports all STU Series DDR3 204Pin SODIMM products.

Some item was being EOL in this list, Please contact with our sales Dep.

Pin Assignments

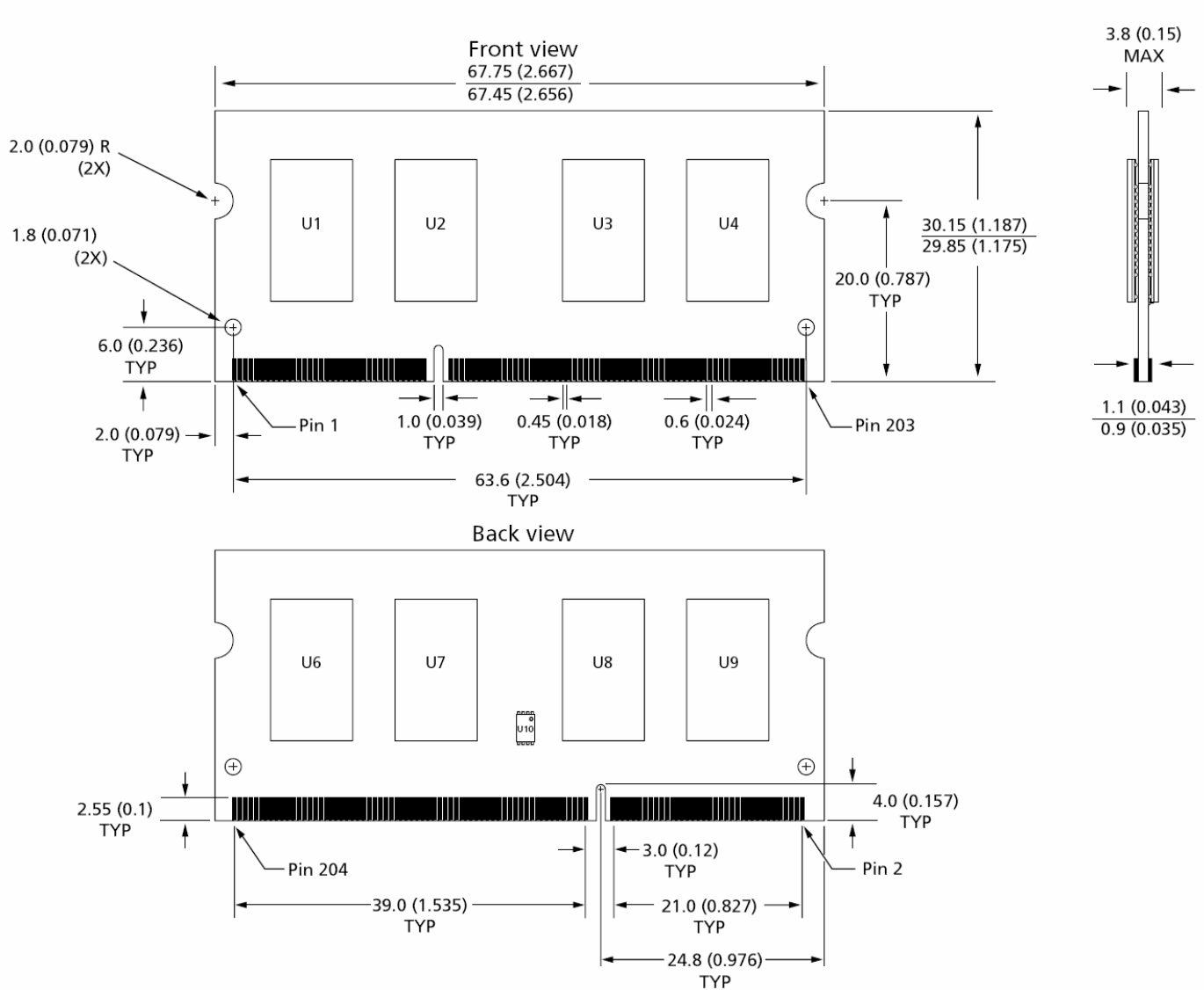
204-Pin DDR3 SODIMM Front							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol
1	VREFDQ	53	DQ19	105	VDD	157	DQ42
3	VSS	55	VSS	107	A10	159	DQ43
5	DQ0	57	DQ24	109	BA0	161	VSS
7	DQ1	59	DQ25	111	VDD	163	DQ48
9	VSS	61	VSS	113	WE#	165	DQ49
11	DM0	63	DM3	115	CAS#	167	VSS
13	VSS	65	VSS	117	VDD	169	DQS6#
15	DQ2	67	DQ26	119	A13	171	DQS6
17	DQ3	69	DQ27	121	S1#	173	VSS
19	VSS	71	VSS	123	VDD	175	DQ50
21	DQ8	73	CKE0	125	NC	177	DQ51
23	DQ9	75	VDD	127	VSS	179	VSS
25	VSS	77	NC	129	DQ32	181	DQ56
27	DQS1#	79	BA2	131	DQ33	183	DQ57
29	DQS1	81	VDD	133	VSS	185	VSS
31	VSS	83	A12	135	DQS4#	187	DM7
33	DQ10	85	A9	137	DQS4	189	VSS
35	DQ11	87	VDD	139	VSS	191	DQ58
37	VSS	89	A8	141	DQ34	193	DQ59
39	DQ16	91	A5	143	DQ35	195	VSS
41	DQ17	93	VDD	145	VSS	197	SA0
43	VSS	95	A3	147	DQ40	199	VDDSPD
45	DQS2#	97	A1	149	DQ41	201	SA1
47	DQS2	99	VDD	151	VSS	203	VTT
49	VSS	101	CK0	153	DM5	-	-
51	DQ18	103	CK0#	155	VSS	-	-

204-Pin DDR3 SODIMM Back							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol
2	VSS	54	VSS	106	VDD	158	DQ46
4	DQ4	56	DQ28	108	BA1	160	DQ47
6	DQ5	58	DQ29	110	RAS#	162	VSS
8	VSS	60	VSS	112	VDD	164	DQ52
10	DQS0#	62	DQS3#	114	S0#	166	DQ53
12	DQS0	64	DQS3	116	ODT0	168	VSS
14	VSS	66	VSS	118	VDD	170	DM6
16	DQ6	68	DQ30	120	ODT1	172	VSS
18	DQ7	70	DQ31	122	NC	174	DQ54
20	VSS	72	VSS	124	VDD	176	DQ55
22	DQ12	74	CKE1	126	VREFCA	178	VSS
24	DQ13	76	VDD	128	SS	180	DQ60
26	VSS	78	NC	130	DQ36	182	DQ61
28	DM1	80	NC/A14	132	DQ37	184	VSS
30	RESET#	82	VDD	134	VSS	186	DQS7#
32	VSS	84	A11	136	DM4	188	DQS7
34	DQ14	86	A7	138	VSS	190	VSS
36	DQ15	88	VDD	140	DQ38	192	DQ62
38	VSS	90	A6	142	DQ39	194	DQ63
40	DQ20	92	A4	144	VSS	196	VSS
42	DQ21	94	VDD	146	DQ44	198	EVENT#
44	VSS	96	A2	148	DQ45	200	SDA
46	DM2	98	A0	150	VSS	202	SCL
48	VSS	100	VDD	152	DQS5#	204	VTT
50	DQ22	102	CK1	154	DQS5	-	-
52	DQ23	104	CK1#	156	VSS	-	-

Pin Description

Symbol	Type	Description
A0–A14	Input	Address inputs: Provide the row address for ACTIVE commands and the column address and auto precharge bit for READ/WRITE commands to select one location out of the memory array in the respective bank. A10 is sampled during a PRECHARGE command to determine whether the PRECHARGE applies to one bank (A10 LOW) or all banks (A10 HIGH). If only one bank is to be precharged, the bank is selected by BA. A12 is sampled during READ and WRITE commands to determine if burst chop (on-the-fly) will be performed. The address inputs also provide the opcode during mode register command set. A0–A13 (128Mx8) A0–A14 (256Mx8).
BA0–BA2	Input	Bank address inputs: BA0, BA1 define to which device bank an ACTIVE, READ, WRITE, or PRECHARGE command is being applied. BA0, BA1 define which mode register, including MR, EMR, EMR(2), and EMR(3), is loaded during the LOAD MODE command.
CK0, CK0#, CK1, CK1#	Input	Clock: CK and CK# are differential clock inputs. All address and control input signals are sampled on the crossing of the positive edge of CK and negative edge of CK#. Output data (DQs and DQS/DQS#) is referenced to the crossings of CK and CK#.
CKE0, CKE1	Input	Clock enable: CKE (registered HIGH) activates and CKE (registered LOW) deactivates clocking circuitry on the DDR3 SDRAM.
DM0–DM7	Input	Data input mask: DM is an input mask signal for write data. Input data is masked when DM is sampled HIGH, along with that input data, during a write access. DM is sampled on both edges of DQS. Although DM pins are input-only, the DM loading is designed to match that of DQ and DQS7pins.
ODT0 ODT1	Input	On-die termination: ODT (registered HIGH) enables termination resistance internal to the DDR3 SDRAM. When enabled, ODT is only applied to the following pins: DQ, DQS, DQS# and DM. The ODT input will be ignored if disabled via the LOAD MODE command.
RAS#, CAS#, WE#	Input	Command inputs: RAS#, CAS#, and WE# (along with S#) define the command being entered.
RESET#	Input (LVCMOS)	Reset: RESET# is an active LOW CMOS input referenced to V _{SS} . The RESET# input receiver is a CMOS input defined as a rail-to-rail signal with DC HIGH $\geq 0.8 \times V_{DD}$ and DC LOW $\leq 0.2 \times V_{DD}$.
S0#, S1#	Input	Chip select: S# enables (registered LOW) and disables (registered HIGH) the command decoder.
SA[2:0]	Input	Presence-detect address inputs: These pins are used to configure the SPD EEPROM address range.
SCL	Input	Serial clock for presence-detect: SCL is used to synchronize the presence-detect data transfer to and from the module.
DQ0–DQ63	I/O	Data input/output: Bidirectional data bus.
DQS0–DQS7 DQS0#–DQS7#	I/O	Data strobe: Output with read data, input with write data for source synchronous operation. Edge-aligned with read data, center-aligned with write data.
SDA	I/O	Serial presence-detect data: SDA is a bidirectional pin used to transfer addresses and data into and out of the SPD EEPROM on the module.
V _{DD}	Supply	Power supply: 1.5V $\pm 0.075V$. The component V _{DD} and V _{DDQ} are connected to the module V _{DD} .
V _{DDSPD}	Supply	Temperature sensor/SPD EEPROM power supply: +3.0V to +3.6V.
V _{REFCA}	Supply	Reference voltage: Control, command, and address (V _{DD} /2).
V _{REFDQ}	Supply	Reference voltage: DQ, DM (V _{DD} /2).
V _{SS}	Supply	Ground.
V _{TT}	Supply	Termination voltage: Used for control, command, and address (V _{DD} /2).
NC	–	No connect: These pins are not connected on the module.
NU	–	Not used: These pins are not used in specific module configuration/operations.

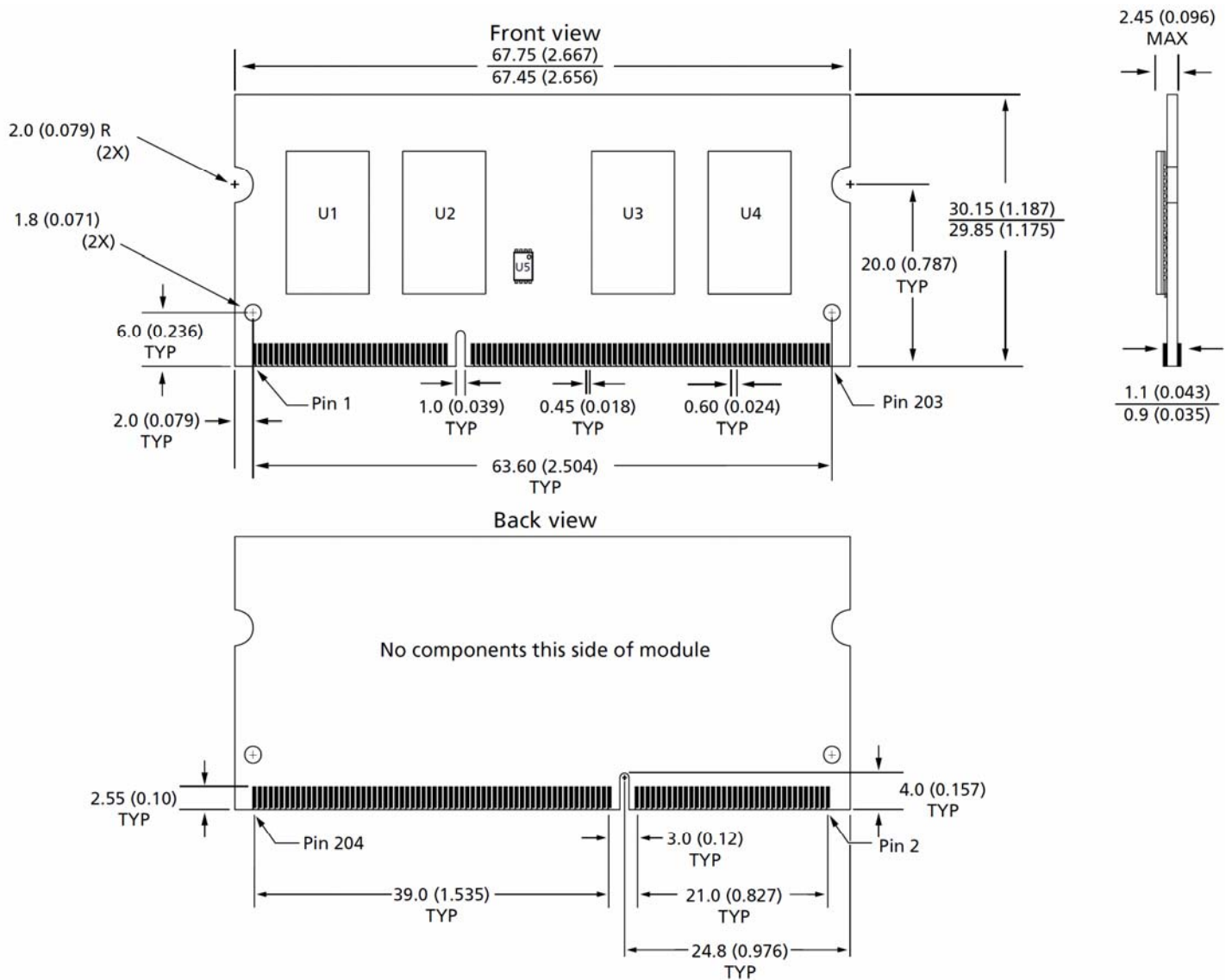
Simplified Mechanical Drawing(x8 1Rank)



Note: 1. All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.

Note: 2. The dimensional diagram is for reference only.

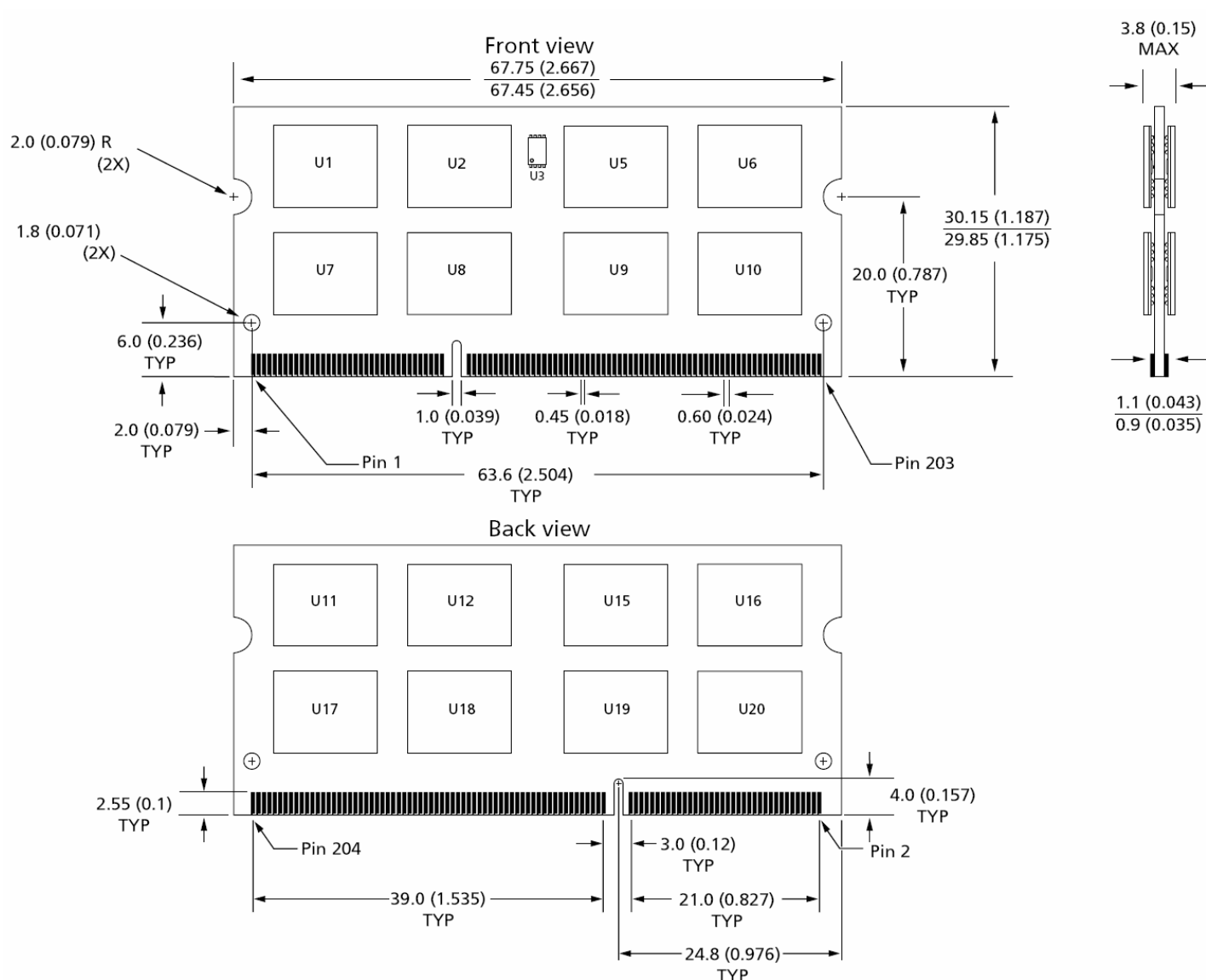
Simplified Mechanical Drawing(x16 1Rank)



Note: 1. All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.

Note: 2. The dimensional diagram is for reference only.

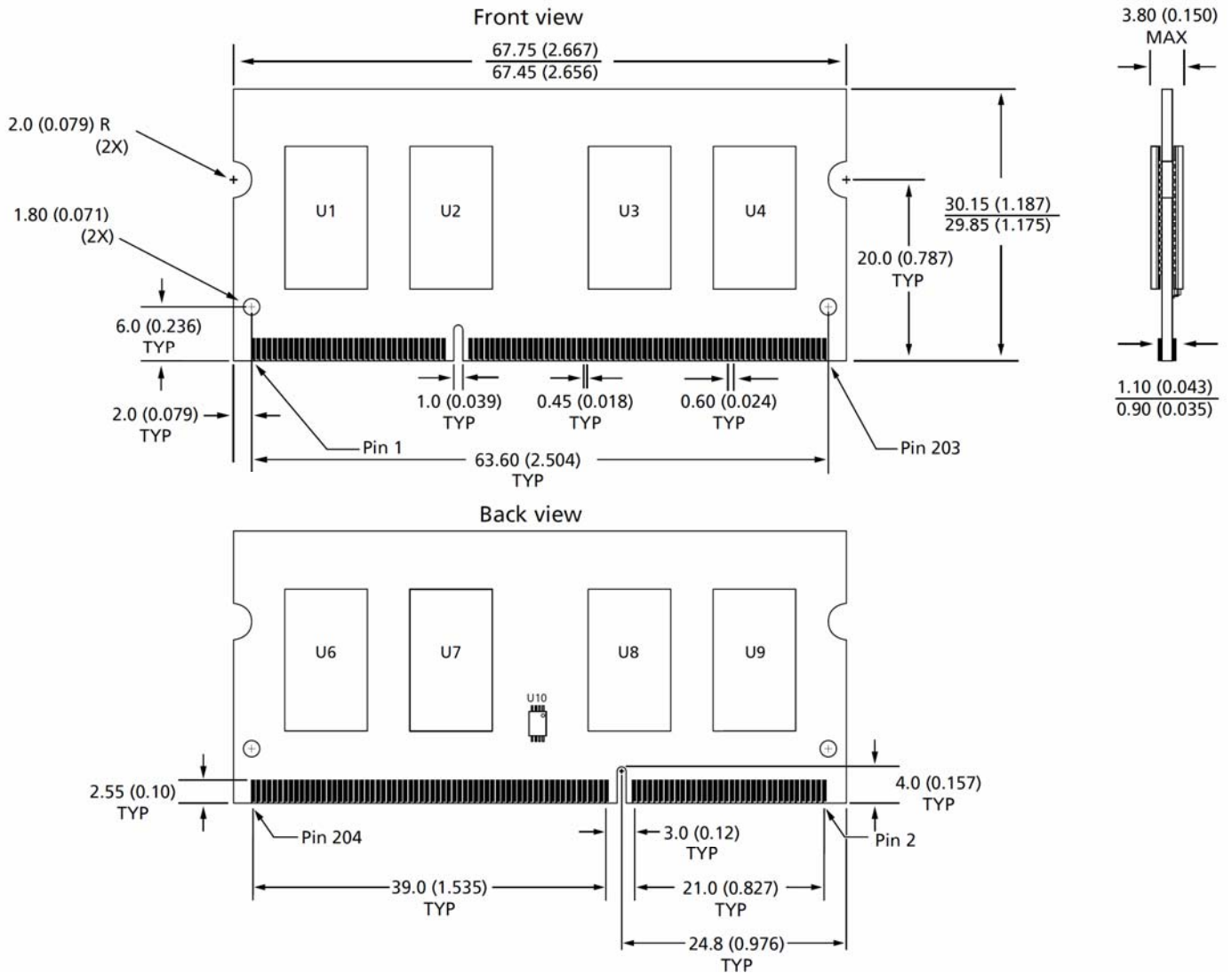
Simplified Mechanical Drawing(x8 2Ranks)



Note 1: All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.

Note 2: The dimensional diagram is for reference only.

Simplified Mechanical Drawing(x16 2Ranks)



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Note 2: The dimensional diagram is for reference only.